

SOD-323 Plastic-Encapsulate Diodes

BAV16WS/1N4148WS FAST SWITCHING DIODES

SOD-323

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FEATURES

Fast Switching Speed
 Surface Mount Package Ideally Suited for
 Automatic Insertion
 For General Purpose Switching Applications
 High Conductance

MARKING: T6, T4

Maximum Ratings and Electrical Characteristics, Single Diode @ $T_A=25^\circ\text{C}$

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V_{RM}	100	V
Peak Repetitive Peak reverse voltage	V_{RRM}	75	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	150	mA
Peak forward surge current @=1.0 μs @=1.0s	I_{FSM}	2.0 1.0	A
Power Dissipation	P_d	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{STG}	-65~+150	$^\circ\text{C}$

Electrical Ratings @ $T_A=25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}			0.715	V	$I_F=1\text{mA}$
	V_{F2}			0.855	V	$I_F=10\text{mA}$
	V_{F3}			1.0	V	$I_F=50\text{mA}$
	V_{F4}			1.25	V	$I_F=150\text{mA}$
Reverse current	I_{R1}			1	μA	$V_R=75\text{V}$
	I_{R2}			25	nA	$V_R=20\text{V}$
Capacitance between terminals	C_T			2	pF	$V_R=0\text{V}, f=1\text{MHz}$
Reverse Recovery Time	t_{rr}			4	ns	$I_F=I_R=10\text{mA}$ $I_{rr}=0.1X I_R, R_L=100\Omega$

Typical Characteristics

BAV16WS/1N4148WS

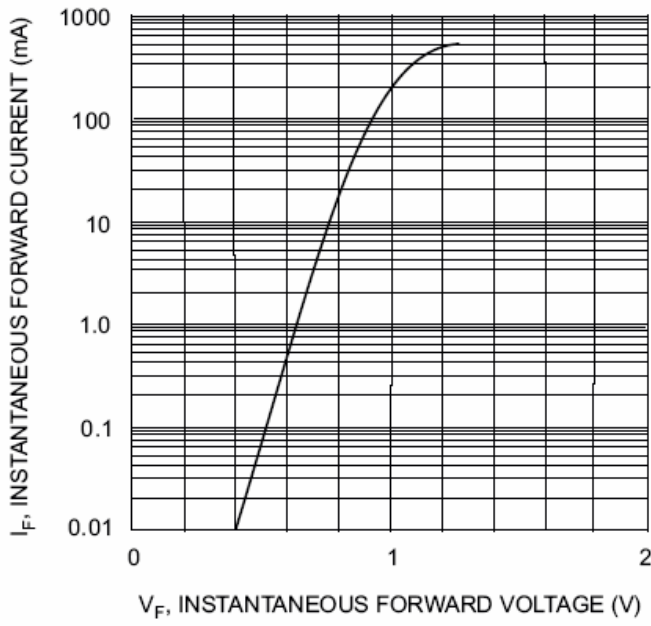


Fig. 1 Forward Characteristics

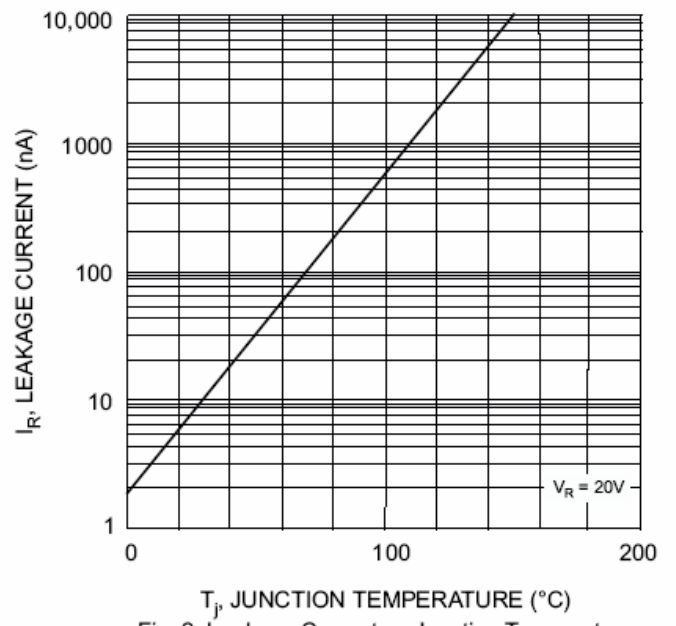


Fig. 2 Leakage Current vs Junction Temperature